4-Output PCIe Gen 4 Clock Buffer for Automotive Applications

Features

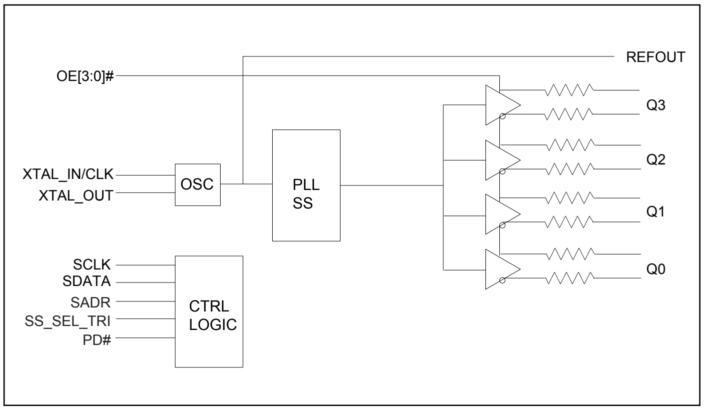
- 1.8V Supply Voltage
- HCSL Input: 100MHz, also support 50MHz or 125MHz via SMBus
- 4 Differential Low Power HCSL Outputs with on-chip Termination
- Individual Output Enable
- Programmable Slew Rate and Output Amplitude for each output
- Differential Outputs blocked until PLL is locked
- Strapping pins or SMBus for configuration
- 3.3V Tolerant SMBus Interface Support
- Very Low Jitter Outputs
  - Differential cycle-to-cycle jitter <50ps (Grade 2)
  - Differential output-to-output skew <50ps
  - PCIe® Gen 1/Gen 2/Gen 3/Gen 4 compliant
- AEC-Q100 qualified, supports Automotive Grade 2 and 1
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ PI6CB184Q is suitable for automotive applications requiring specific change control; this part is AEC-Q100 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities. https://www.diodes.com/quality/product-definitions/
- Packaging (Pb-free & Green):
  - 32-contact TQFN 5×5mm (SWP) with Sidewall Plating

Description

The PI6CB184Q is an 4-output very low power PCIe Gen 1/Gen 2/Gen 3/Gen 4 clock buffer. It takes an reference input to fanout four 100MHz low power differential HCSL outputs with on-chip terminations. The on-chip termination can save 16 external resistors and make layout easier. Individual OE pin for each output provides easier power management.

It uses proprietary PLL design to achieve very low jitter that meets PCIe Gen 1/Gen 2/Gen 3/Gen 4 requirements. Other than PCIe 100MHz support, this device also support Ethernet application with 50MHz or 125MHz via SMBus. It provides various options such as different slew rate and amplitude through strapping pins or SMBUS so that users can configure the device easily to get the optimized performance for their individual boards. This device is optimized for Automotive designs.

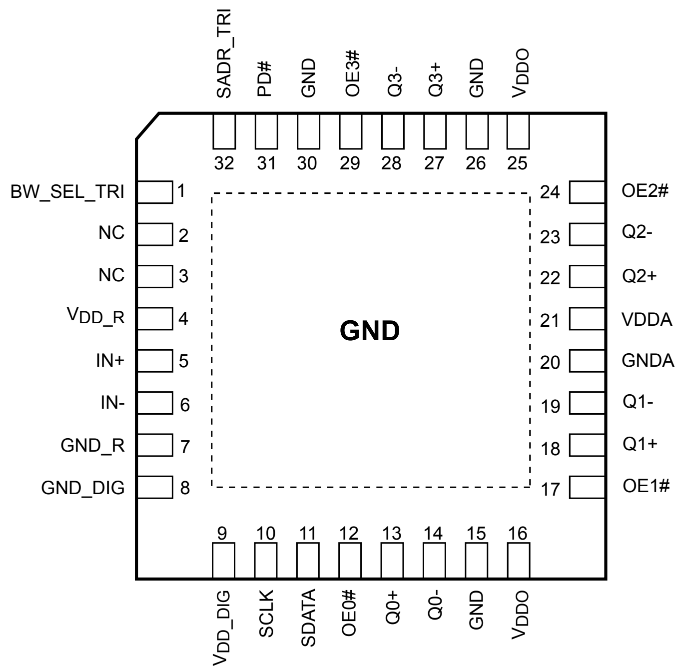
Block Diagram



Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Configuration



Pin Description

Pin Number	Pin Name	Type		Description
1	BW_SEL_TRI	Input	Tri-level	Latch to select low loop bandwidth, bypass PLL, and high loop bandwidth. This pin has both internal pull-up and pull-down
2	NC			Internal connected for feedback loop. Do not connect this pin
3	NC			Internal connected for feedback loop. Do not connect this pin
4	V_{DD}_R	Power		Power supply for input differential buffers
5	IN+	Input		Differential true clock input
6	IN-	Input		Differential complementary clock input
7	GND_R	Power		Ground for input differential buffers
8	GND_DIG	Power		Ground for digital circuitry
9	V_{DD}_DIG	Power		Power supply for digital circuitry, nominal 1.8V
10	SCLK	Input	CMOS	SMBUS clock input, 3.3V tolerant
11	SDATA	Input/ Output	CMOS	SMBUS Data line, 3.3V tolerant
12	OE0#	Input	CMOS	Active low input for enabling Q0 pair. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
13	Q0+	Output	HCSL	Differential true clock output

Pin Description Cont.

Pin Number	Pin Name	Type		Description
14	Q0-	Output	HCSL	Differential complementary clock output
15, 26, 30	GND	Power		Ground
16, 25	V_{DDO}	Power		Power supply for differential outputs
17	OE1#	Input	CMOS	Active low input for enabling Q1 pair. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
18	Q1+	Output	HCSL	Differential true clock output
19	Q1-	Output	HCSL	Differential complementary clock output
20	GNDA	Power		Ground for analog circuitry
21	V_{DDA}	Power		Power supply for analog circuitry
22	Q2+	Output	HCSL	Differential true clock output
23	Q2-	Output	HCSL	Differential complementary clock output
24	OE2#	Input	CMOS	Active low input for enabling Q2 pair. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
27	Q3+	Output	HCSL	Differential true clock output
28	Q3-	Output	HCSL	Differential complementary clock output
29	OE3#	Input	CMOS	Active low input for enabling Q3 pair. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
31	PD#	Input	CMOS	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal pull-up resistor.
32	SADR_TRI	Input	Tri-level	Latch to select SMBus Address. This pin has an internal pull-down

SMBus Address Selection Table

	SADR	Address	+Read/Write Bit
State of SADR on first application of PD#	0	1101011	X
	M	1101100	X
	1	1101101	X

Power Management Table

PD#	IN	SMBus OE bit	OEn#	Qn+	Qn-	PLL Status
0	X	X	X	Low	Low	Off
1	Running	0	X	Low	Low	On(1)
1	Running	1	0	Running	Running	On(1)
1	Running	1	1	Low	Low	On(1)

Note:
1. If PLL Bypass mode is selected, the PLL will be off and outputs will be running.

PLL Operating Mode Select Table

BW_SEL_TRI	Operating Mode	Byte1 [7:6] Readback	Byte1 [4:3] Readback
0	PLL with low Bandwidth	00	00
M	PLL Bypass	01	01
1	PLL with high Bandwidth	11	11

Frequency Select Table

Freq. Select Byte 3 [4:3]	IN (MHz)	Qn (MHz)
00 (default)	100	100
01	50	50
10	125	125
11	Reserved	Reserved

Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature.. –65°C to +150°C
Supply Voltage to Ground Potential, V_{DDxx} ....–0.5V to +2.5V
Input Voltage .... –0.5V to V_{DD}+0.5V, not exceed 2.5V
SMBus, Input High Voltage 3.6V
ESD Protection (HBM) 2000V
ESD Protection (CDM) PD# pin #31 only 250V
ESD Protection (CDM) all other pins..500V
Max Junction Temperature .... +135°C

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Operating Conditions

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V_{DD}, V_{DDA}, V_{DD_R}, V_{DD_DIG}	Power Supply Voltage		1.7	1.8	1.9	V
V_{DDO}	Output Power Supply Voltage		1.7	1.8	1.9	V
I_{DDA}	Analog Power Supply Current	V_{DDA} + V_{DD_R}, PLL mode, All outputs active @100MHz		11	15	mA
I_{DD}	Power Supply Current	V_{DD} + V_{DD_DIG}, All outputs active @100MHz		8	10	mA
I_{DDO}	Power Supply Current for Outputs	All outputs active @100MHz		17	25	mA
I_{DDA_PD}	Analog Power Supply Power Down(1) Current	V_{DDA} + V_{DD_R}, PLL mode, All outputs active @100MHz		0.7	1	mA
I_{DD_PD}	Power Supply Power Down(1) Current	V_{DD} + V_{DD_DIG+} V_{DDO}, All outputs LOW/LOW			1.2	mA
T_A	Ambient Temperature	Automotive grade 2	–40		105	°C
		Automotive grade 1	–40		125	

Note:
1. Input clock is not running.

Input Electrical Characteristics

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
R_{pu}	Internal Pull up Resistance			120		KΩ
R_{dn}	Internal Pull down Resistance			120		KΩ
L_{PIN}	Pin Inductance				7	nH

SMBus Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V_{DDSMB}	Nominal Bus Voltage		1.7		3.6	V
V_{IHSMB}	SMBus Input High Voltage	SMBus, V_{DDSMB} = 3.3V	2.1		3.6	V
		SMBus, V_{DDSMB} < 3.3V	0.65 V_{DDSMB}			
V_{ILSMB}	SMBus Input Low Voltage	SMBus, V_{DDSMB} = 3.3V			0.6	V
		SMBus, V_{DDSMB} < 3.3V			0.6	
$I_{SMBSINK}$	SMBus Sink Current	SMBus, at V_{OLSMB}	4			mA
V_{OLSMB}	SMBus Output Low Voltage	SMBus, at $I_{SMBSINK}$			0.4	V
f_{MAXSMB}	SMBus Operating Frequency	Maximum frequency			400	kHz
t_{RMSB}	SMBus Rise Time	(Max V_{IL} - 0.15) to (Min V_{IH} + 0.15)			1000	ns
t_{FMSB}	SMBus Fall Time	(Min V_{IH} + 0.15) to (Max V_{IL} - 0.15)			300	ns

LVCMOS DC Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V_{IH}	Input High Voltage	Single-ended inputs, except SMBus	0.75 V_{DD}		V_{DD} +0.3	V
V_{IM}	Input Mid Voltage	SADR_TRI, BW_SEL_TRI	0.4V_{DD}	0.5V_{DD}	0.6V_{DD}	V
V_{IL}	Input Low Voltage	Single-ended inputs, except SMBus	-0.3		0.25 V_{DD}	V
I_{IH}	Input High Current	Single-ended inputs, $V_{IN} = V_{DD}$			20	uA
I_{IL}	Input Low Current	Single-ended inputs, V_{IN} = 0V	-20			µA
I_{IH}	Input High Current	Single-ended inputs with pull up / pull down resistor, $V_{IN} = V_{DD}$			220	uA
I_{IL}	Input Low Current	Single-ended inputs with pull up / pull down resistor, V_{IN} = 0V	-220			µA
C_{IN}	Input Capacitance		1.5		5	pF

LVCMOS AC Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
t_{OELAT}	Output enable latency	Q start after OE# assertion Q stop after OE# deassertion	1		3.5	clocks
t_{PDLAT}	PD# de-assertion	Differential outputs enable after PD# de-assertion		20	300	us

HCSL Input Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V_{IHDIF}	Diff. Input High Voltage(3)	IN+, IN-, single-end measurement	600	800	1150	mV
V_{ILDIF}	Diff. Input Low Voltage(3)	IN+, IN-, single-end measurement	-300	0	300	mV
V_{COM}	Diff. Input Common Mode Voltage		150		1000	mV
V_{SWING}	Diff. Input Swing Voltage	Peak to peak value (V_{IHDIF} - V_{ILDIF})	300		1450	mV
f_{INBP}	Input Frequency	PLL Bypass mode	1		200	MHz
f_{IN100}	Input Frequency	100MHz PLL	60	100	110	MHz
f_{IN125}	Input Frequency	125MHz PLL	75	125	137.5	MHz
f_{IN156}	Input Frequency	50MHz PLL	30	50	65	MHz
t_{STAB}	Clock Stabilization	From V_{DD} Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock		0.6	1.0	ms
t_{RF}	Diff. Input Slew Rate(2)	Measured differentially	0.4			V/ns
I_{IN}	Diff. Input Leakage Current	$V_{IN} = V_{DD}$, V_{IN} = GND	-5	0.01	5	uA
t_{DC}	Diff. Input Duty Cycle	Measured differentially	45		55	%
tj_{c-c}	Diff. Input Cycle to cycle jitter	Measured differentially			125	ps

Note:

1. Guaranteed by design and characterization, not 100% tested in production
2. Slew rate measured through +/-75mV window centered around differential zero
3. The device can be driven by a single-ended clock by driving the true clock and biasing the complement clock input to the Vbias, where Vbias is (V_{IH}-V_{IL})/2

HCSL Output Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Typ.	Max.	Units
V_{OH}	Output Voltage High(1)	Statistical measurement on single-ended signal using oscilloscope math function	660	774	950	mV
V_{OL}	Output Voltage Low(1)		-150		150	mV
V_{OMAX}	Output Voltage Maximum(1)	Measurement on single ended signal using absolute value		821	1150	mV
V_{OMIN}	Output Voltage Minimum(1)		-300	-15		mV
V_{OSWING}	Output Swing Voltage(1,2,3)	Scope averaging off	300	1536		mV
V_{OC}	Output Cross Voltage(1,2,4)		250	430	550	mV
DV_{OC}	V_{OC} Magnitude Change(1,2,5)			12	140	mV

Note:
1. At default SMBUS amplitude settings
2. Guaranteed by design and characterization, not 100% tested in production
3. Measured from differential waveform
4. This one is defined as voltage where Q+ = Q- measured on a component test board and only applied to the differential rising edge
5. The total variation of all Vcross measurements in any particular system. This is a subset of Vcross_min/max allowed.

HCSL Output AC Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Typ.	Max.	Units
f_{OUT}	Output Frequency			100		MHz
BW	PLL Bandwidth(1,8)	-3dB point in High Bandwidth Mode	2	2.7	4	MHz
		-3dB point in Low Bandwidth Mode	1	1.4	2	MHz
tj_{peak}	PLL Jitter Peaking	Peak pass band gain		1.2	2	dB
t_{RF}	Slew Rate(1,2,3)	Scope averaging on fast setting (Grade 2)	2.1	3	6.5	V/ns
		Scope averaging on fast setting (Grade 1)	1.85	4	7.5	V/ns
		Scope averaging on slow setting (Grade 2)	0.4	2	3	V/ns
		Scope averaging on slow setting (Grade 1)	0.35	2.5	4	V/ns
Dt_{RF}	Slew Rate Matching(1,2,4)	Scope averaging on		3		%
t_{SKEW}	Output Skew(1,2)	Averaging on, V_T = 50%		43	60	ps
t_{PDELAY}	Propagation Delay	PLL Bypass mode, V_T = 50% (Grade 2)	3000	3600	4500	ps
		PLL Bypass mode, V_T = 50% (Grade 1)	3000	4500	5500	ps
		PLL mode, V_T = 50%	0	90	200	ps
tj_{c-c}	Cycle to cycle jitter(1,2)	Grade 2		14	50	ps
		Grade 1		30	70	

HCSL Output AC Characteristics Cont.

Symbol	Parameters	Condition	Min.	Typ.	Max.	Units
tj_{PHASE}	Integrated phase jitter (RMS) (1,5,6)	PCIe Gen 1	20	22	86	ps
		PCIe Gen 2 Low Band, 10kHz < f < 1.5MHz	0.2	0.3	3.0	ps
		PCIe Gen 2 High Band, 1.5MHz < f < Nyquist (50MHz)	1.6	2.0	3.1	ps
		PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)	0.3	0.35	1.0	ps
		125MHz, 1.5MHz to 20MHz, -20dB/decade Rollover < 1.5MHz, -40dB/decade rolloff > 10MHz(9)		1.9	2	ps
tj_{PHASEA}	Additive Integrated phase jitter (RMS)(1,5,10)	PCIe Gen 1		0.6	5	ps
		PCIe Gen 2 Low Band, 10kHz < f < 1.5MHz		0.1	0.3	ps
		PCIe Gen 2 High Band, 1.5MHz < f < Nyquist (50MHz)		0.05	0.1	ps
		PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)		0.05	0.1	ps
		PCIe Gen 4 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz) (BW_SEL_TRI=M)		0.03	0.05	ps
		125MHz, 1.5MHz to 20MHz, -20dB/decade Rollover < 1.5MHz, -40dB/decade rolloff > 10MHz		0.15	0.3	ps
t_{DC}	Duty Cycle(1,2)	Measured differentially, PLL Mode	45	50	55	%
t_{DCD}	Duty Cycle Distortion(1,7)	Measured differentially, PLL Bypass Mode at 100MHz	-1	0	1	%
$t_{STARTUP}$	Start up Time				10	ms
t_{LOCK}	PLL lock Time				20	ms

Note:

1. Guaranteed by design and characterization, not 100% tested in production
2. Measured from differential waveform
3. Slew rate is measured through the Vswing voltage range centered around differential 0V, within +/-150mV window
4. Slew rate matching is measured using a +/-75mV window centered at differential zero
5. See http://www.pcisig.com for complete specs
6. Sample size of at least 100k cycles. This can be extrapolated to 108ps pk-pk @ 1M cycles for a BER of 10^{-12}
7. Duty cycle distortion is the difference in duty cycle between the out and input clock when te device is operated in the PLL bypass mode
8. The Min and Max values of each BW setting track each other, low BW max will never occur with high BW min
9. Applies to all differential outputs
10. For additive jitter RMS value is calculated by the following equation = SQRT [(total jitter)^{*2} - (input jitter)^{*2}]

SMBus Serial Data Interface

PI6CB184Q is a slave only device that supports block read and block write protocol using a single 7-bit address and read/write bit as shown below.

Read and write block transfers can be stopped after any complete byte transfer.

Address Assignment

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	See SBMus Address Selection table			1/0

Note: SMBus address is latched on SADR pin

How to Write

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit		8 bits	1 bit	1 bit
Start bit	Add.	W(0)	Ack	Beginning Byte location = N	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack	....	Data Byte (N+X-1)	Ack	Stop bit

How to Read

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit
Start bit	Address	W(0)	Ack	Beginning Byte location = N	Ack	Repeat Start bit	Address	R(1)	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack

	8 bits	1 bit	1 bit
....	Data Byte (N+X-1)	NAck	Stop bit

Byte 0: Output Enable Register(1)

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	Reserved			1		
6	Q3_OE	Q6 output enable	RW	1	Low/Low	Enabled
5	Q2_OE	Q5 output enable	RW	1	Low/Low	Enabled
4	Reserved			1		
3	Q1_OE	Q3 output enable	RW	1	Low/Low	Enabled
2	Reserved			1		
1	Q0_OE	Q1 output enable	RW	1	Low/Low	Enabled
0	Reserved			1		

Note:
1. A low on these bits will override the OE# pins and force the differential outputs to Low/Low states

Byte 1: PLL Operating Mode and Output Amplitude Control Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	PLLMODERB1	PLL Mode Readback Bit1	R	Latch	See PLL Operating Mode Table	
6	PLLMODERB0	PLL Mode Readback Bit0	R	Latch		
5	PLLMODE_SWCTR	Enable SW control of PLL Mode	RW	0	Values in B1[7:6] set PLL Mode	Values in B1[4:3] set PLL Mode
4	PLLMODE1	PLL Mode control Bit1	RW(1)	0	See PLL Operating Mode Table	
3	PLLMODE0	PLL Mode control Bit0	RW(1)	0		
2	Reserved			1		
1	Amplitude1	Control output amplitude	RW	1	'00' = 0.6V, '01' = 0.7V, '10' = 0.8V, '11' = 0.9V	
0	Amplitude0		RW	0		

Note:
1. B1[5] must be set to a 1 for these bits to have any effect on the part

Byte 2: Differential Output Slew Rate Control Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	Reserved			1		
6	SLEWRATECTR_Q3	Control slew rate of Q6	RW	1	Slow setting	Fast setting
5	SLEWRATECTR_Q2	Control slew rate of Q5	RW	1	Slow setting	Fast setting
4	Reserved			1		
3	SLEWRATECTR_Q1	Control slew rate of Q3	RW	1	Slow setting	Fast setting
2	Reserved			1		
1	SLEWRATECTR_Q0	Control slew rate of Q1	RW	1	Slow setting	Fast setting
0	Reserved			1		

Byte 3: Frequency Select Control Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	Reserved			1		
6	Reserved			1		
5	FREQ_SEL_EN	Enable SW selection of frequency	RW	0	SW Freq. selection disabled	SW Freq. selection enabled
4	FSEL1	Freq. Select Bit 1	RW(1)	0	See Frequency Select Table	
3	FSEL0	Freq. Select Bit 0	RW(1)	0		
2	Reserved			1		
1	Reserved			1		
0	SLEWRATESEL FB	Adjust Slew Rate of Feedback signal	RW	1	2.0V/ns	3.0V/ns

Note:
1. B1[5] must be set to a 1 for these bits to have any effect on the part

Byte 4: Reserved

Bit	Control Function	Description	Type	Power Up Condition	0	1
7:0	Reserved			1		

Byte 5: Revision and Vendor ID Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	RID3	Revision ID	R	0	rev = 0000	
6	RID2		R	0		
5	RID1		R	0		
4	RID0		R	0		
3	PVID3	Vendor ID	R	0	Pericom = 0011	
2	PVID3		R	0		
1	PVID3		R	1		
0	PVID3		R	1		

Byte 6: Device Type/Device ID Register

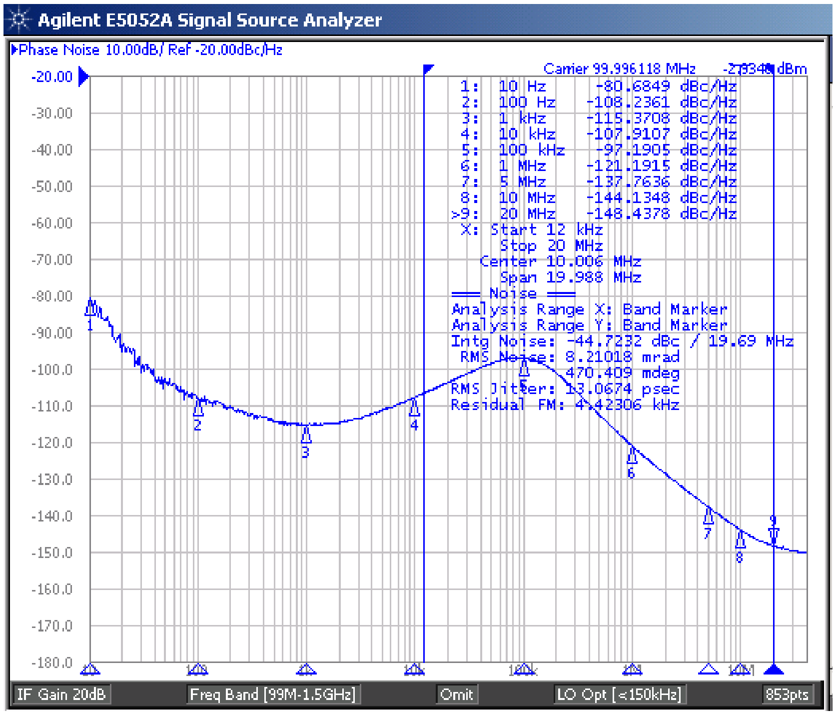
Bit	Control Function	Description	Type	Power Up Condition	0	1
7	DTYPE1	Device type	R	0	'00' = CG, '01' = ZDB,	
6	DTYPE0		R	1	'10' = Reserve, '11' = ZDB	
5	DID5	Device ID	R	0	000100 binary, 04Hex	
4	DID4		R	0		
3	DID3		R	0		
2	DID2		R	1		
1	DID1		R	0		
0	DID0		R	0		

Byte 7: Byte Count Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	Reserved			0		
6	Reserved			0		
5	Reserved			0		
4	BC4	Byte count programming	RW	0	Writing to this register will configure how many bytes will be read back, default is 8 bytes	
3	BC3		RW	1		
2	BC2		RW	0		
1	BC1		RW	0		
0	BC0		RW	0		

Plots

100MHz HCSL Clock



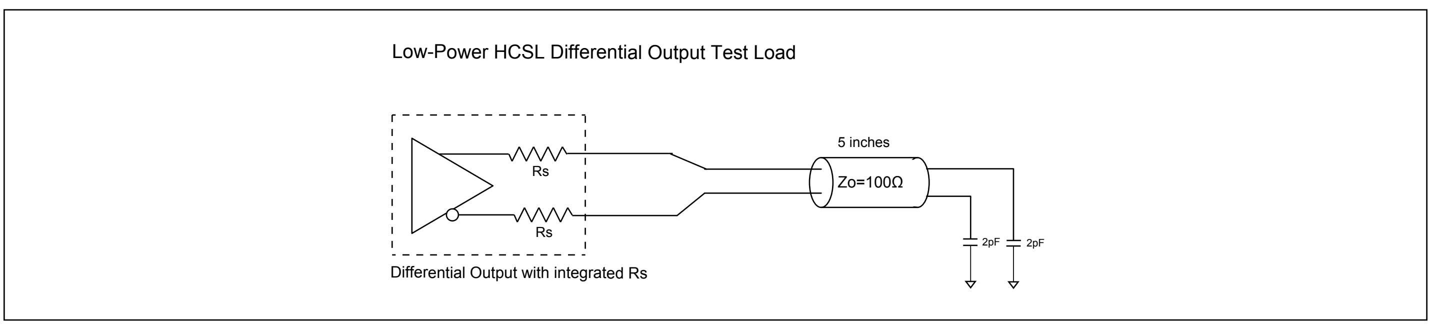


Figure 1. Low Power HCSL Test Circuit

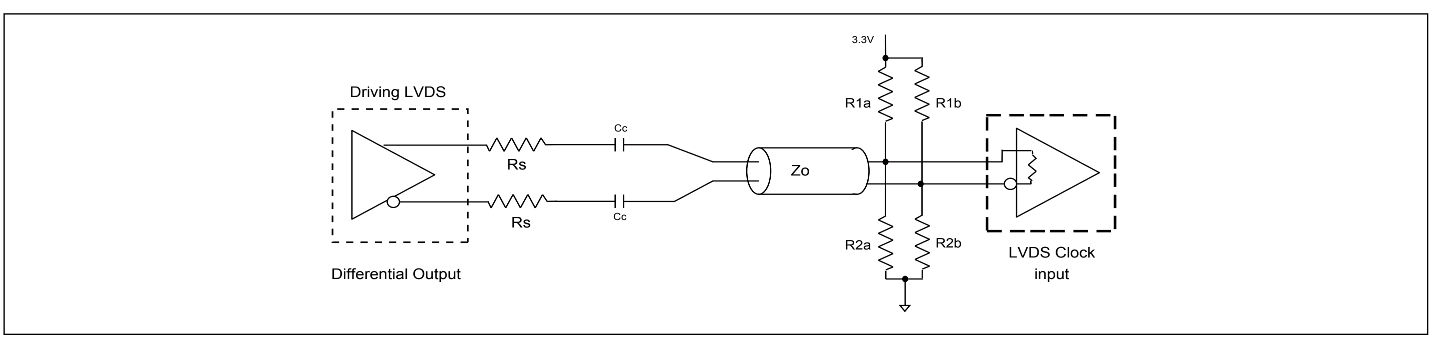


Figure 2. Differential Output driving LVDS

Alternate Differential Output Terminations

Component	Receiver with termination	Receiver without termination	Unit
R_{1a}, R_{1b}	10,000	140	Ω
R_{2a}, R_{2b}	5,600	75	Ω
C_C	0.1	0.1	μF
V_{CM}	1.2	1.2	V

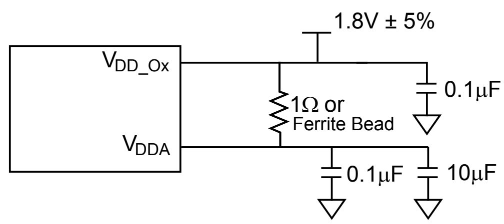
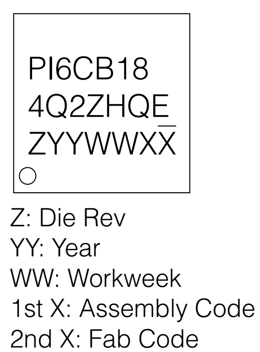


Figure 3. Power Supply Filter

Part Marking

PI6CB184Q2 ZHQ Package

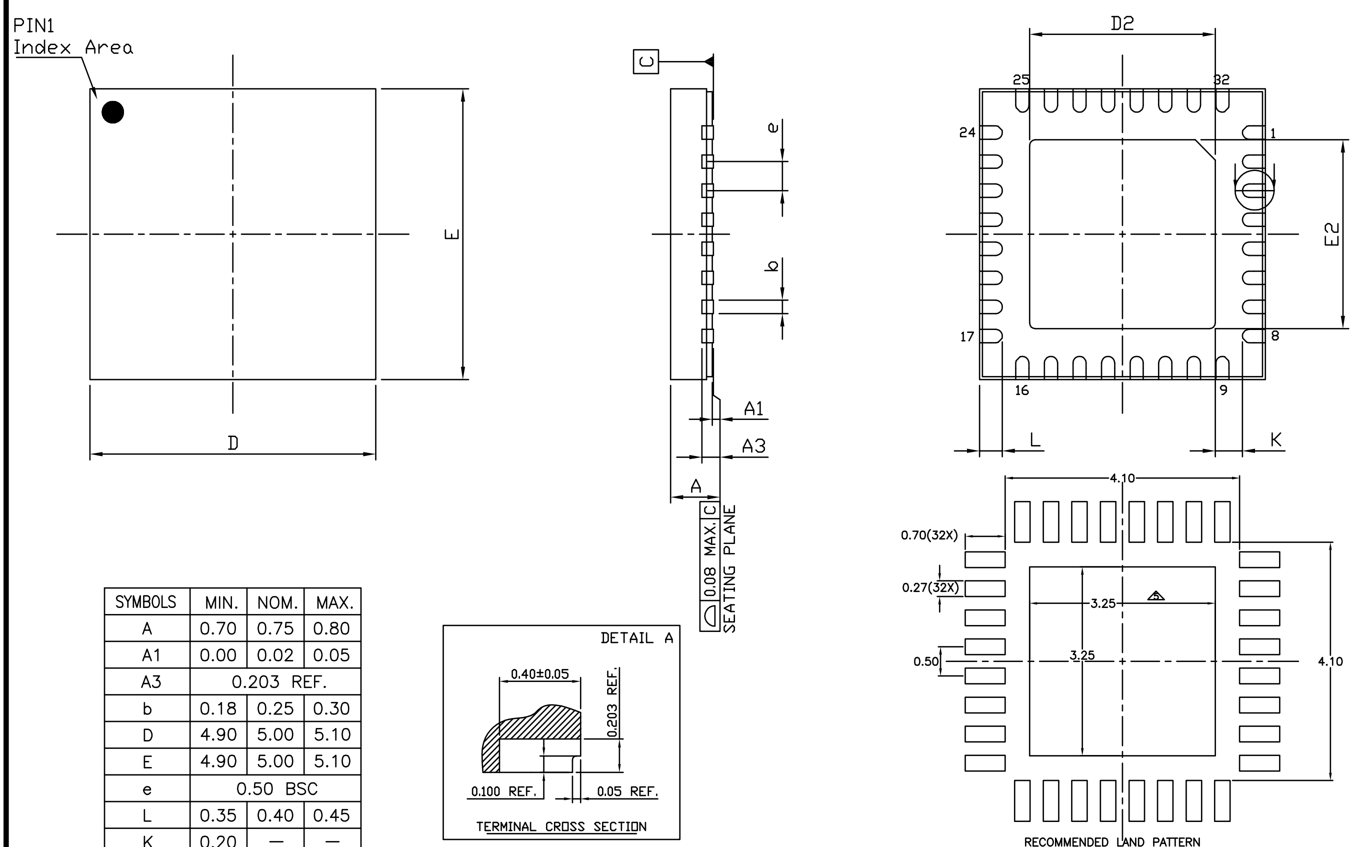


PI6CB184Q1 ZHQ Package

Top mark not available at this time. To obtain advance information regarding the top mark, please contact your local sales representative.

Packaging Mechanical

32-TQFN (ZHQ)



SYMBOLS	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A3	0.203 REF.		
b	0.18	0.25	0.30
D	4.90	5.00	5.10
E	4.90	5.00	5.10
e	0.50 BSC		
L	0.35	0.40	0.45
K	0.20	—	—
D2	3.20	3.25	3.30
E2	3.20	3.25	3.30

NOTE :
1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
2. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
3. REFER JEDEC MO-220.
4. RECOMMENDED LAND PATTERN IS FOR REFERENCE ONLY.
5. THERMAL PAD SOLDERING AREA (MESH STENCIL DESIGN IS RECOMMENDED)
6. SWP STANDS FOR SIDEWALL PLATING

DIODES INCORPORATED — PERICOM A PRODUCT LINE OF DIODES INCORPORATED — ENABLING SERIAL CONNECTIVITY

DATE: 10/08/20

DESCRIPTION: 32-Contact, TQFN 5x5mm (SWP)

PACKAGE CODE: ZHQ (ZHQ32)

DOCUMENT CONTROL #: PD-2234 REVISION: A

20-1335

For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

Ordering Code	Package Code	Package Description	Operating Temperature
PI6CB184Q2ZHQEX	ZHQ	32-contact, TQFN 5×5mm (SWP)	-40 to 105°C
PI6CB184Q1ZHQEX	ZHQ	32-contact, TQFN 5×5mm (SWP)	-40 to 125°C

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Q = Automotive Compliant
5. 1 and 2 = AEC-Q100 Grade Level
6. E = Pb-free and Green
7. X suffix = Tape/Reel

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